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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/710,732	07/30/2004	Ko-Hsing Chang	13041-US-PA	4731
31561	7590	03/07/2006	EXAMINER	
JIANQ CHYUN INTELLECTUAL PROPERTY OFFICE 7 FLOOR-1, NO. 100 ROOSEVELT ROAD, SECTION 2 TAIPEI, 100 TAIWAN			HARRISON, MONICA D	
			ART UNIT	PAPER NUMBER
			2813	
DATE MAILED: 03/07/2006				

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/710,732

Applicant(s)

CHANG ET AL.

Examiner

Monica D. Harrison

Art Unit

2813

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 13 September 2005.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-20 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____.

DETAILED ACTION

1. Applicant's amendment filed 9/13/05 has been entered.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-20 are rejected under 35 U.S.C. 102(e) as being anticipated by Yang (6,569,700 B2).

2. Regarding claim 1, Yang discloses a method of fabricating a photodiode (Figure 2, reference 60), comprising the steps of: providing a substrate (Figure 2, reference 44); forming a well region of a first conductive type in the substrate (Figure 2, reference 50); forming an isolation structure in the substrate to define a photosensitive area on the substrate (Figure 2, reference 46); forming a plurality of trenches in the well region of the substrate within the photosensitive area (Figure 3, reference 58); and forming a doped layer of a second conductive type over the substrate, wherein the doped layer covers the interior walls of the trenches and the surface of the substrate within the photosensitive area (Figure 4, reference 52).

3. Regarding claim 2, Yang discloses wherein forming the doped layer comprises performing an annealing operation (column 3, lines 36-49).

4. Regarding claim 3, Yang discloses wherein the annealing operation drives the dopants within the doped layer of the second conductive type into the substrate and makes

Art Unit: 2813

junction of the first conductive type and the second conductive type shift into the substrate (column 3, lines 36-49).

5. Regarding claim 4, Yang discloses wherein the first conductive type is P-type (Figure 2, reference 44) and the second conductive type is N-type (Figure 2, reference 50).

6. Regarding claim 5, Yang discloses wherein the first conductive type is N-type (Figure 2, reference 50) and the second conductive type is P-type (Figure 2, reference 52).

7. Regarding claim 6, Yang discloses wherein the step of forming the doped layer comprises performing a chemical vapor deposition process (column 2, lines 51-65).

8. Regarding claim 7, Yang discloses wherein material constituting the doped layer is selected from the group consisting of doped polysilicon and doped epitaxial silicon (Figure 4, reference 66).

9. Regarding claim 8, Yang discloses wherein the doped layer completely fills the trenches (Figure 2, reference 52).

10. Regarding claim 9, Yang discloses wherein the method further comprises forming a buffer layer over the substrate covering the interior walls of the trenches as well as the surface of the substrate within the photosensitive area after forming the trenches in the substrate within the photosensitive area (Figure 4, reference 66).

11. Regarding claim 10, Yang discloses wherein the step of forming the buffer layer comprises performing a chemical vapor deposition process (column 2, lines 51-65).

12. Regarding claim 11, Yang discloses wherein material constituting the buffer layer is selected from the group consisting of polysilicon and epitaxial silicon (Figure 4, reference 66).

13. Regarding claim 12, Yang discloses wherein after forming the doped layer over the substrate further comprises performing an annealing operation (column 3, lines 36-49).

14. Regarding claim 13, Yang discloses wherein the annealing operation drives the dopants within the doped layer into the buffer layer so that a junction of the second conductivity type and the first conductive type is formed within the buffer layer (column 3, lines 36-49).

15. Regarding claim 14, Yang discloses wherein the annealing operation drives the dopants within the doped layer into the substrate so that a junction of the second conductive type and the first conductive type is formed within the substrate (column 3, lines 36-49).

16. Regarding claim 15, Yang discloses wherein the doped layer completely fills the trenches (Figure 2, reference 52).

17. Regarding claim 16, Yang discloses a method of fabricating a photodiode (Figure 2, reference 60), comprising the steps of: providing a substrate (Figure 2, reference 44); forming a well region of a first conductive type in the substrate (Figure 2, reference 50); forming an isolation structure in the well region of the substrate to define a photosensitive area on the substrate (Figure 2, reference 46); forming a plurality of trenches in the substrate within the photosensitive area (Figure 3, reference 58); forming a buffer layer over the substrate, wherein the buffer layer covers the interior walls of the trenches and the surface of the substrate within the photosensitive area (Figure 4, reference 66); forming a doped layer of a second conductive type over the buffer layer (Figure 2, reference 52); and performing an annealing operation to drive dopants within the doped layer into the buffer layer and form a junction of the second conductive type and the first conductive type within the buffer layer (column 2, lines 66-67 thru column 3, lines 1-10).

18. Regarding claim 17, Yang discloses performing a chemical vapor deposition process (column 2, lines 51-65).

19. Regarding claim 18, Yang discloses wherein material constituting the doped layer is selected from the group consisting doped polysilicon and doped epitaxial silicon (Figure 4, reference 66).

20. Regarding claim 19, Yang discloses wherein the step of forming the buffer layer further comprises performing a chemical vapor deposition process (column 2, lines 51-65).

21. Regarding claim 20, Yang discloses wherein material constituting the buffer layer is selected from the group consisting of polysilicon and epitaxial silicon (Figure 4, reference 66).

Response to Arguments

22. Applicant's arguments with respect to claims 1-20 have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica D. Harrison whose telephone number is 571-272-1959. The examiner can normally be reached on M-F 7:00am-3:30pm.


If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr. can be reached on 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 2813

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Monica D. Harrison
AU 2813

mdh
February 24, 2006


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